



MBR20100

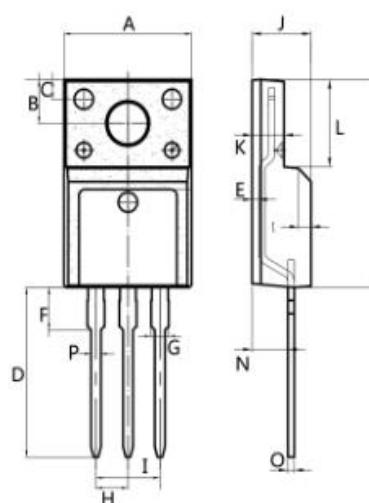
Low VF Schottky Barrier Rectifiers

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O. Flame Retardant Epoxy Molding Compound.
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency.
- High current capability
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.
- Lead free in comply with EU RoHS

MECHANICAL DATA

- Case: TO-220 & ITO-220 molded plastic
- Terminals: Solder plated, solderable per MIL-STD -750, Method 2026
- Polarity: As marked.
- Mounting Position: Any



Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84

All Dimensions in millimeter

Maximum Ratings (Per Leg) @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	100	V
Maximum rms voltage	V_{RMS}	70	V
Maximum average forward rectified current per device per diode	$I_{F(AV)}$	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I_{FSM}	150	A
Typical junction capacitance ($V_R=4\text{V}$, $f=1\text{MHz}$)	C_J	620	pF
Typical thermal resistance per diode (Note 1)	$R_{θJC}$	2	°C/W
Operating junction temperature range	T_J	-55 to + 150	°C

Note : 1. Mounted on infinite heatsink.

ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage per diode	V_{BR}	$I_R=0.5\text{mA}$	100	-	-	V
Instantaneous forward voltage per diode	V_F	$I_F=3\text{A}$ $I_F=5\text{A}$ $I_F=10\text{A}$ $T_J=25^\circ\text{C}$	- - -	0.47 0.53 0.67	- - 0.75	V
		$I_F=3\text{A}$ $I_F=5\text{A}$ $I_F=10\text{A}$ $T_J=125^\circ\text{C}$	- - -	0.4 0.49 0.61	- - -	V
		$V_R=70\text{V}$	-	5	-	μA
Reverse current per diode	I_R	$V_R=100\text{V}$ $T_J=25^\circ\text{C}$ $T_J=125^\circ\text{C}$	- -	7.2	50 -	μA mA



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Characteristic Curves ($T_A = 25^\circ C$ unless otherwise noted)

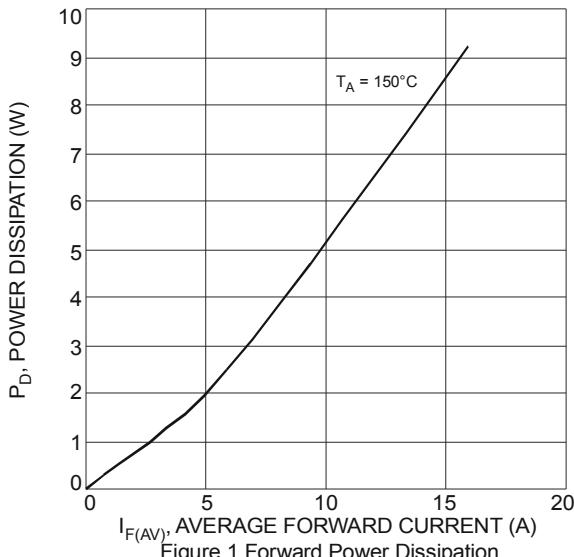


Figure 1 Forward Power Dissipation

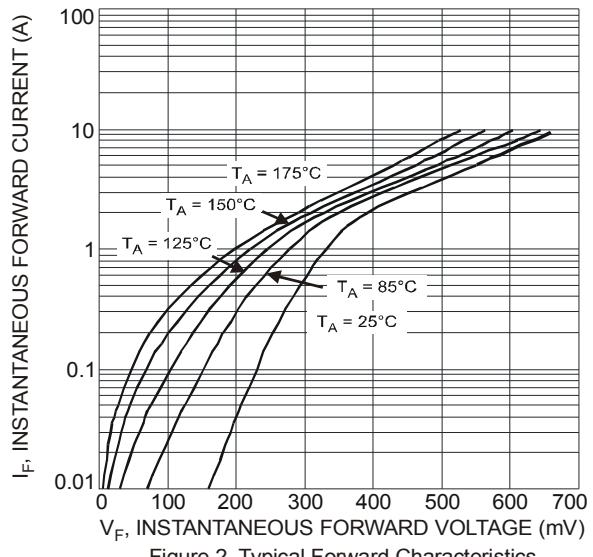


Figure 2 Typical Forward Characteristics

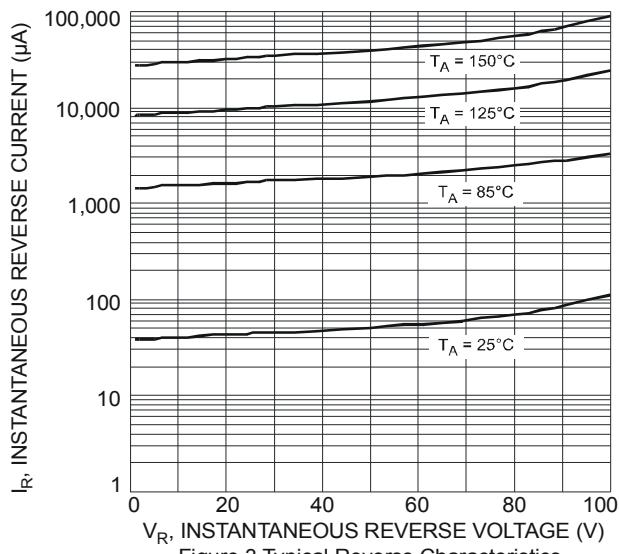


Figure 3 Typical Reverse Characteristics

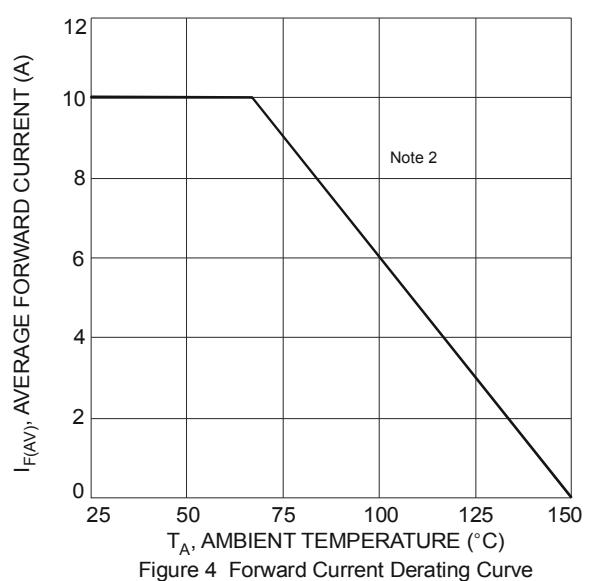


Figure 4 Forward Current Derating Curve